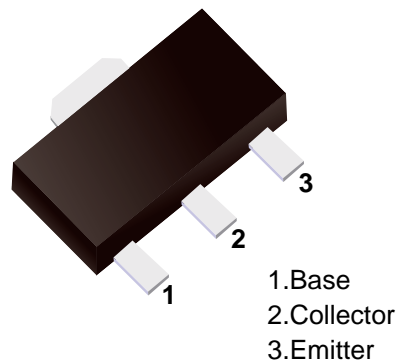


■ NPN Transistors

■ Features

- Excellent h_{FE} characteristics



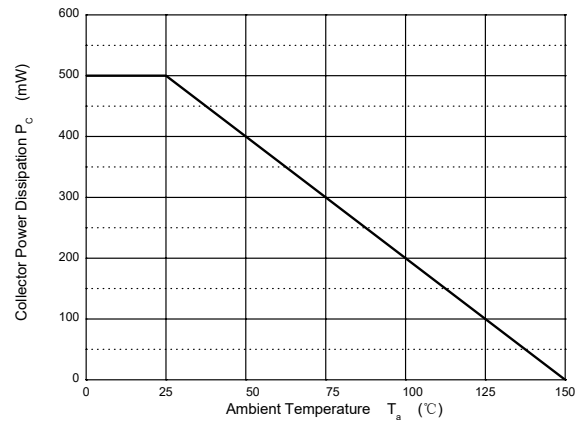
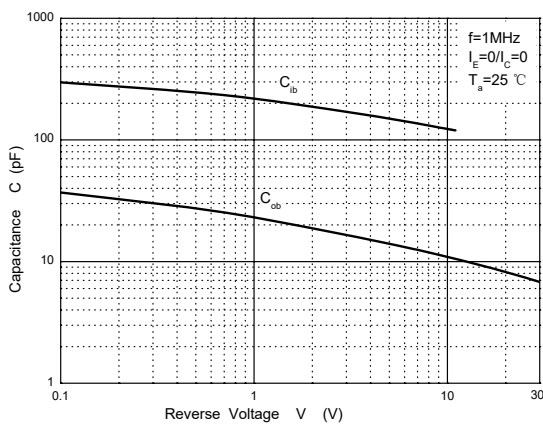
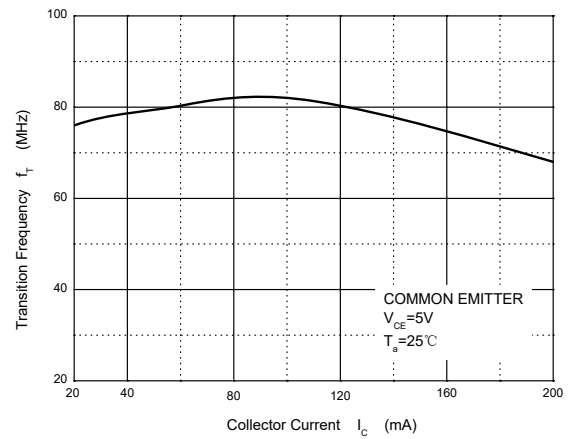
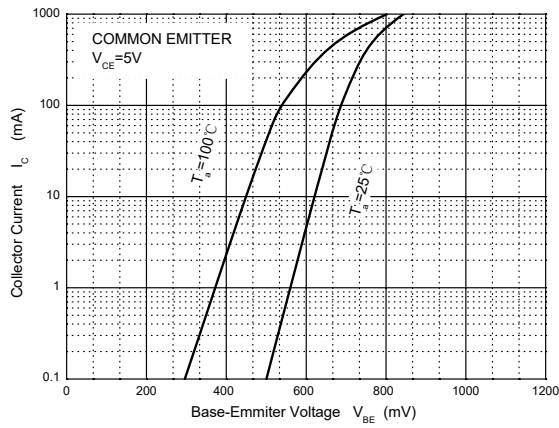
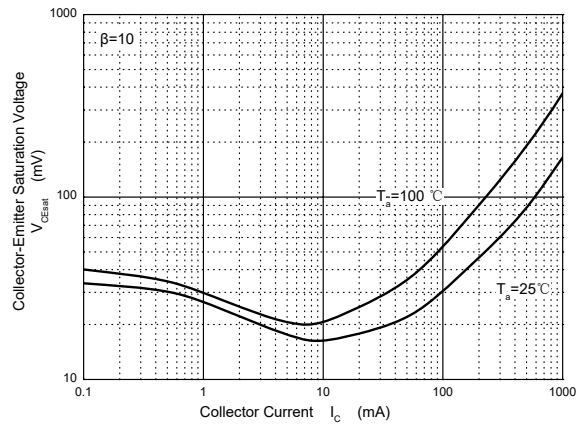
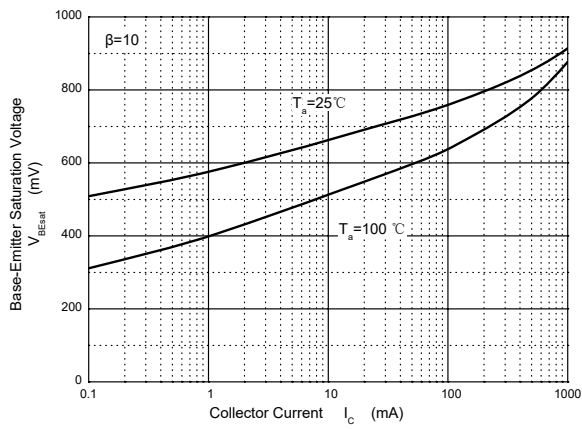
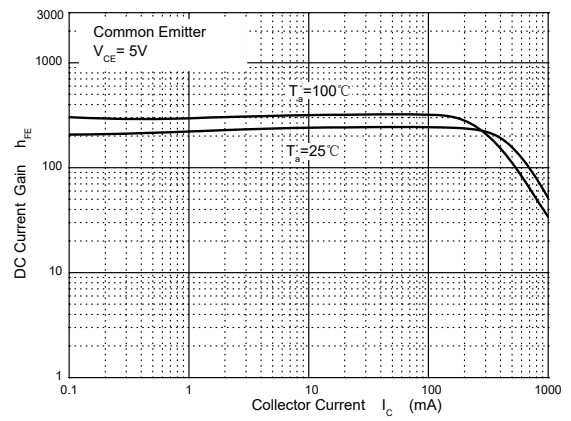
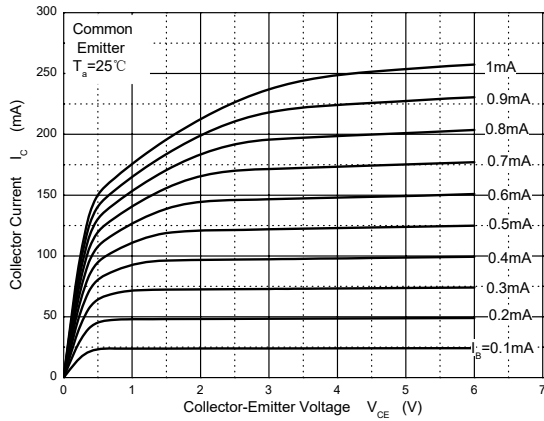
■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

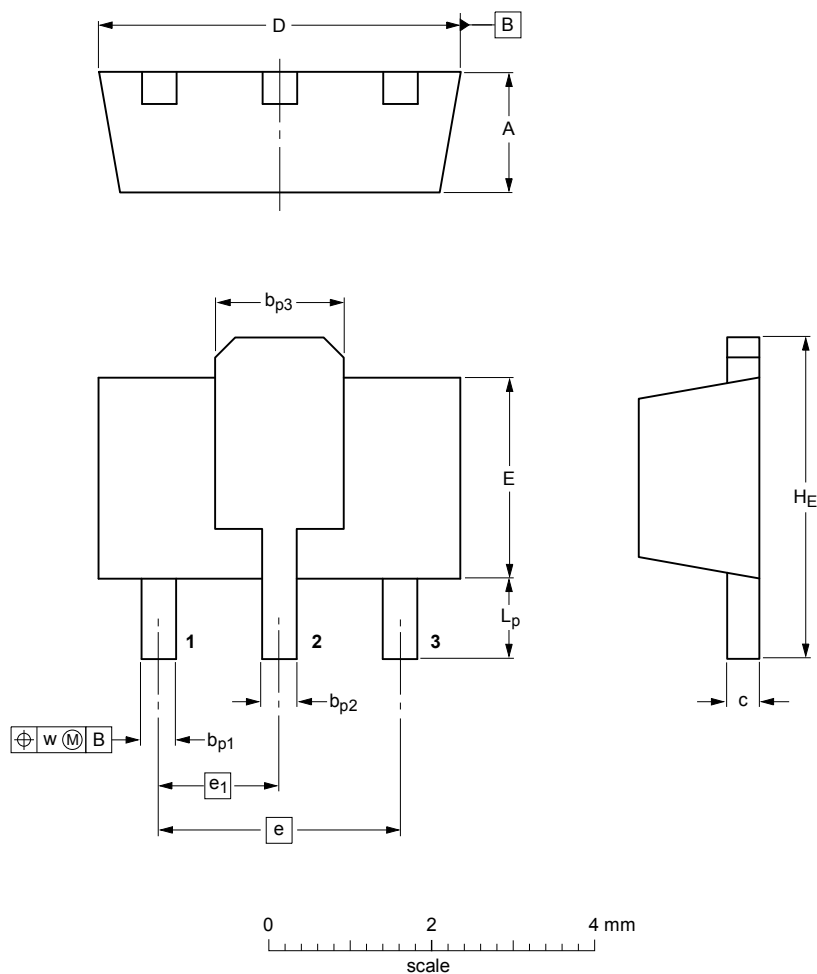
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	160	V
Collector Emitter Voltage	V_{CEO}	160	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	1	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 200\text{ mA}$ Current Gain Group O Y	h_{FE}	100	-	200	-
	h_{FE}	160	-	320	-
Collector Base Cutoff Current at $V_{CB} = 150\text{ V}$	I_{CBO}	-	-	1	μA
Emitter Base Cutoff Current at $V_{EB} = 6\text{ V}$	I_{EBO}	-	-	1	μA
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	160	-	-	V
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	-	1.5	V
Base Emitter on Voltage at $I_C = 5\text{ mA}$, $V_{CE} = 5\text{ V}$	$V_{BE(on)}$	0.45	-	0.75	V
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 200\text{ mA}$	f_T	20	100	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	-	20	pF



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4					